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b) Amendments to the Claims

Please cancel claim 3 and amend claims 1, 4, 12, 20 and 23 as follows. A detailed listing of the status of the claims that are or were in the application is provided.

--1. (Currently Amended) A method of manufacturing material comprising the steps of:

(A) contacting a solution containing a solvent, silicon and surfactant with a substrate ~~for controlling alignment of an opposing surface of an overcoated layer thereon~~ having alignment control ability to the surfactant; and

(B) drying said ~~coated~~ substrate to remove the solvent contained in said solution ~~and form a porous material~~ for forming a material having uniaxially aligned channel structures, wherein the channel structures comprise the surfactant and wherein the channel structures are substantially parallel to the substrate surface ~~in which the surfactant is held within the porous material~~.

2. (Original) A method according to claim 1, wherein silicon is contained in said solution in a state of compound.

3. (Cancelled)

4. (Currently Amended) A method of manufacturing material, comprising the steps of:

coating a substrate having alignment control ability ~~capable of controlling alignment of an opposing surface of an overcoated layer thereon~~ to a surfactant with a ~~surfactant~~ solution containing silicon alkoxide and the surfactant; and

drying said coated substrate to form a ~~porous~~ material ~~with an~~ having uniaxially aligned channel structures, wherein the channel structures comprise the surfactant and wherein the channel structures are substantially parallel to the substrate surface ~~in which the surfactant is held within the porous material~~.

5. (Previously Amended) A method according to claim 4, wherein the step of coating the substrate is a step of selectively coating a desired portion of said substrate with said solution in a desired pattern and, after the drying step, a patterned mesostructured silica is formed.

6. (Previously Amended) A method according to claim 4 or 5, wherein said substrate is a silicon single crystal substrate having (110) orientation.

7. (Original) A method according to claim 4 or 5, wherein said substrate is a substrate whose surface is coated with a polymer compound film subjected to a rubbing process.

8. (Original) A method according to claim 4 or 5, wherein said substrate is a substrate whose surface is coated with a Langmuir-Blodgett film of polymer compound.

9. (Previously Amended) A method according to any one of claims 4 or 5, wherein the substrate is coated with the surfactant solution by a pen lithography method.

10. (Previously Amended) A method according to any one of claims 4 or 5, wherein the substrate is coated with the surfactant solution by an ink jet method.

11. (Previously Amended) A method according to any one of claims 4 or 5, wherein the substrate is coated with the surfactant solution by a dip coating method.

12. (Currently Amended) A method of manufacturing material, comprising the steps of:

coating a substrate having alignment control ability ~~capable of controlling alignment of an opposing surface of an overcoated layer thereon~~ to a surfactant with a solution ~~of surfactant~~ containing a silicon ~~alkoxides~~ alkoxide and the surfactant;

drying said coated substrate to form a ~~porous~~ material having uniaxially aligned channel structures, wherein the channel structures comprise the surfactant and wherein the channel structures are substantially parallel to the substrate surface ~~in which the surfactant is held within the porous material~~; and, thereafter,

removing the surfactant.

13. (Previously Amended) A method according to claim 12, wherein said step of coating said substrate with said solution is a step of selectively coating a desired portion of said substrate with said solution in a desired pattern.

14. (Previously Amended) A method according to claim 12 or 13, wherein said substrate is a silicon single crystal substrate having (110) orientation.

15. (Original) A method according to claim 12 or 13, wherein said substrate is a substrate whose surface is coated with a polymer compound film subjected to a rubbing process.

16. (Original) A method according to any one of claims 12 or 13, wherein said substrate is a substrate whose surface is coated with a Langmuir-Blodgett film of polymer compound.

17. (Previously Amended) A method according to any one of claims 12 or 13, wherein said substrate is coated with said surfactant solution by a pen lithography method.

18. (Previously Amended) A method according to any one of claims 12 or 13, wherein said substrate is coated with said surfactant solution by an ink jet method.

19. (Previously Amended) A method according to any one of claims 12 or 13, wherein said substrate is coated with said surfactant solution by a dip coating method.

20. (Currently Amended) A method of manufacturing material, comprising the steps of:

(A) contacting a substrate having alignment control ability to a surfactant with ~~attaching~~ a solution containing a solvent, silicon and the surfactant ~~to a substrate for controlling alignment of an opposing surface of an overcoated layer thereon~~; and

(B) drying said substrate ~~to which said solution is attached to remove the solvents contained in said solution and~~ to form a ~~porous~~ material having uniaxially aligned channel structures, wherein the channel structures comprise the surfactant and wherein the channel structures are substantially parallel to the substrate surface ~~in which the surfactant is held within the porous material attached to said substrate~~.

21. (Original) A method according to claim 20, wherein silicon is contained in said solution in the form of compound.

22. (Original) A method according to claim 20, wherein silicon is contained in said solution as silicon alkoxides.

23. (Currently Amended) A method of manufacturing material comprising the steps of:

(A) ~~contacting~~ coating a substrate having alignment control ability to a surfactant with a solution containing a solvent, silicon and the surfactant ~~with a substrate~~; and

(B) drying said coated substrate ~~in contact with the solution to remove the solvent and~~ to form a ~~porous~~ material ~~which has~~ having uniaxially aligned channel structures, wherein the channel structures comprise the surfactant and wherein the channel structures are substantially parallel to the substrate surface ~~and pores in which the surfactant is held~~.

24. (Previously Added) A method according to Claim 1, further comprising the step of removing said surfactant.--